

ABSTRACT OF THE DISCLOSURE

In a method for manufacturing a semiconductor device according to the present invention, a back surface on a silicon wafer is ground and, after that, mirror-finished. A breakable layer on a back surface is removed. A silicon wafer is formed in the silicon wafer has a back surface in which a crystalline layer which is disposed innermore than the breakable layer is exposed. Bumps are formed on predetermined positions on a surface on the silicon wafer. By doing this, it is possible to provide a semiconductor device and a method for manufacturing therefore in which it is possible to prevent a crack from being formed on the semiconductor base board caused by a stress in a process for forming the bumps. As a result, it is possible to improve the production yield in the process for forming the bumps. Also, it is possible to realize more integration in the semiconductor device by a lower production cost.